

Silicon NPN Epitaxial

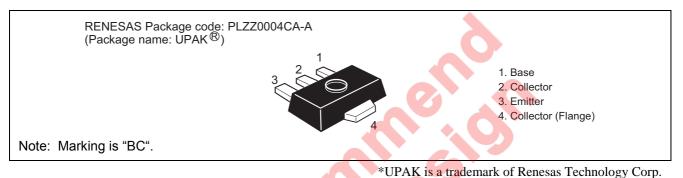
REJ03G0785-0200 (Previous ADE-208-1147) Rev.2.00 Aug.10.2005

## Application

## • Low frequency power amplifier

• Complementary pair with 2SB1001

## Outline



# **Absolute Maximum Ratings**

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Collector to base voltage	V <sub>CBO</sub>	20	V
Collector to emitter voltage	V <sub>CEO</sub>	16	V
Emitter to base voltage	V <sub>EBO</sub>	6	V
Collector current	Ι <sub>C</sub>	2	А
Collector peak current	i <sub>C(peak)</sub> * <sup>1</sup>	3	А
Collector power dissipation	Pc*2	1	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	С°

Notes: 1. PW  $\leq$  10 ms, Duty cycle  $\leq$  20%.

2. Value on the alumina ceramic board (12.5  $\times$  20  $\times$  0.7 mm)

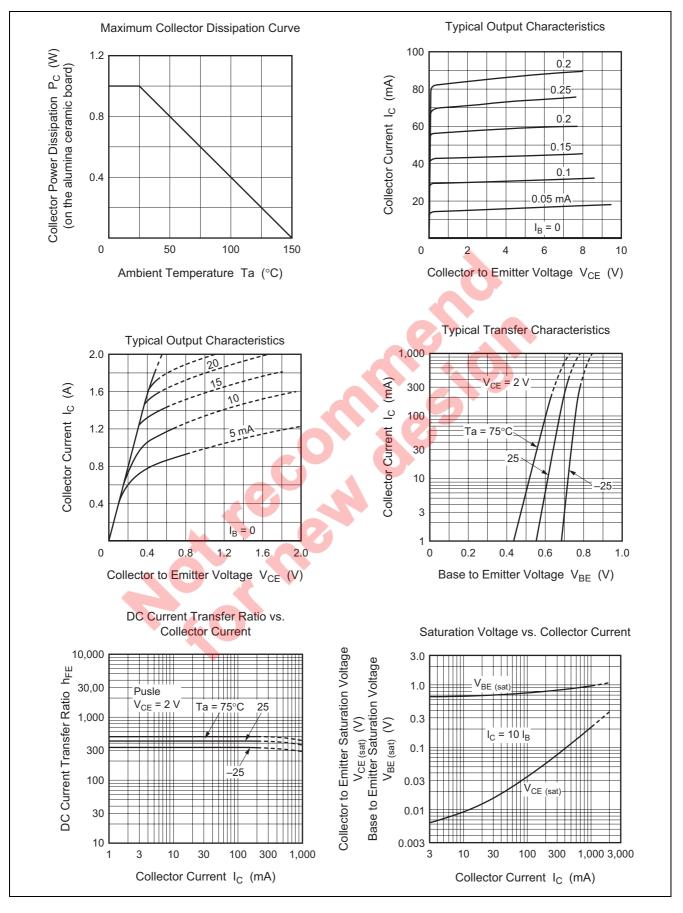


# **Electrical Characteristics**

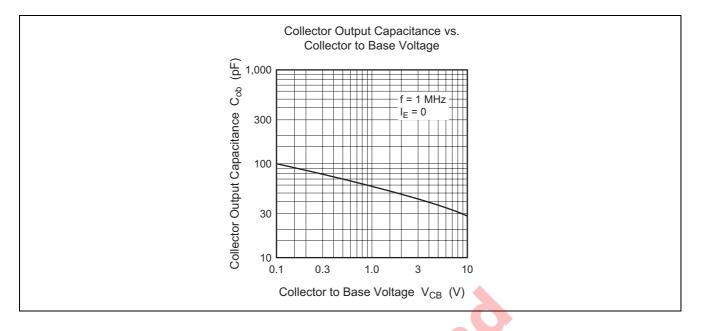
						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	V <sub>(BR)CBO</sub>	20	—		V	$I_{\rm C}$ = 10 $\mu$ A, $I_{\rm E}$ = 0
Collector to emitter breakdown voltage	V <sub>(BR)CEO</sub>	16	—		V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	V <sub>(BR)EBO</sub>	6	—		V	$I_{E} = 10 \ \mu A, I_{C} = 0$
Collector cutoff current	I <sub>CBO</sub>	_	_	0.1	μA	$V_{CB} = 16 \text{ V}, \text{ I}_{E} = 0$
Emitter cutoff current	I <sub>EBO</sub>	_		0.1	μA	$V_{EB} = 5 V, I_{C} = 0$
DC current transfer ratio	$h_{FE}$	250	_	500		$V_{CE}$ = 2 V, $I_C$ = 0.1 A, Pulse
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	_	0.15	0.3	V	$I_{C}$ = 1 A, $I_{B}$ = 0.1 A, Pulse
Base to emitter saturation voltage	V <sub>BE(sat)</sub>	_	0.9	1.2	V	$I_{C}$ = 1 A, $I_{B}$ = 0.1 A, Pulse
Gain bandwidth product	f⊤	_	100		MHz	$V_{CE}$ = 2 V, $I_{C}$ = 10 mA
Collector output capacitance	Cob	_	20		pF	$V_{CB}$ = 10 V, I <sub>E</sub> = 0, f = 1 MHz



## **Main Characteristics**

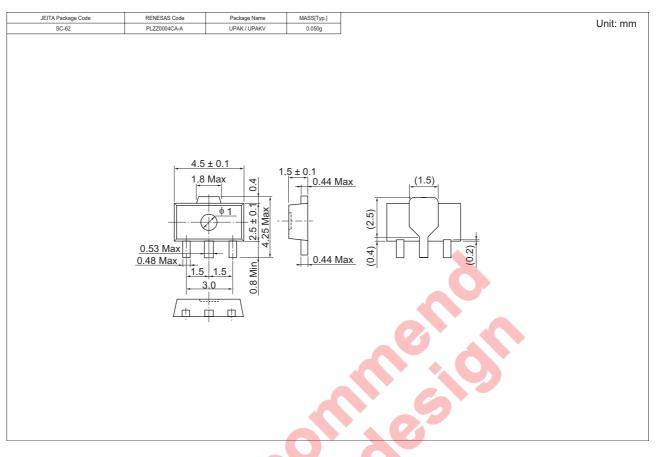








## **Package Dimensions**



## **Ordering Information**

Part Name	Quantity	Shipping Container
2SD1367BCTR-E	1000	§ 178 mm Reel, 12 mm Emboss Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.



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